



1/6

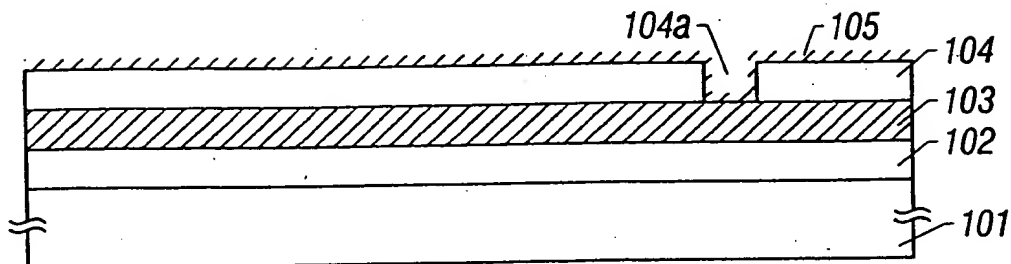


FIG. 1A

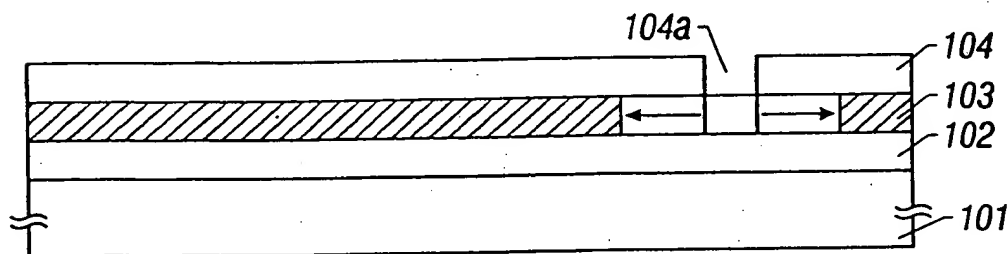


FIG. 1B

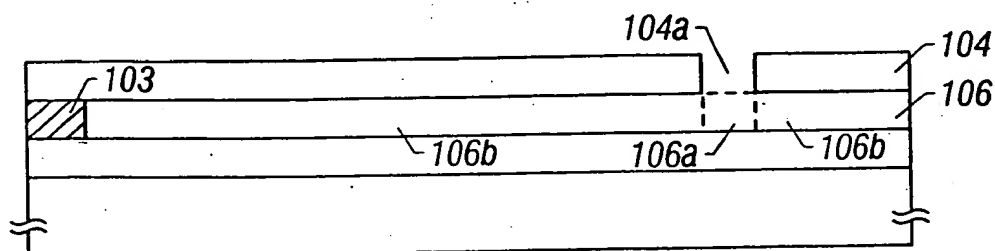


FIG. 1C

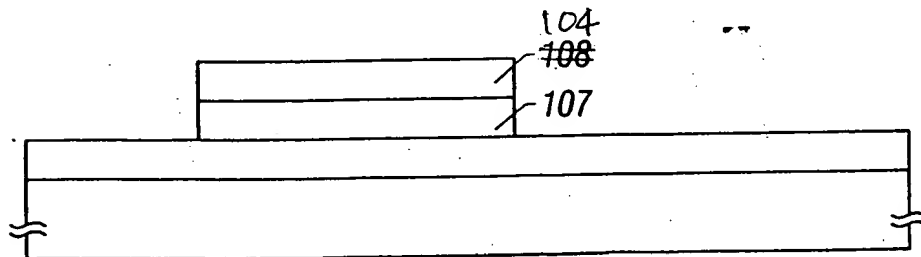


FIG. 1D

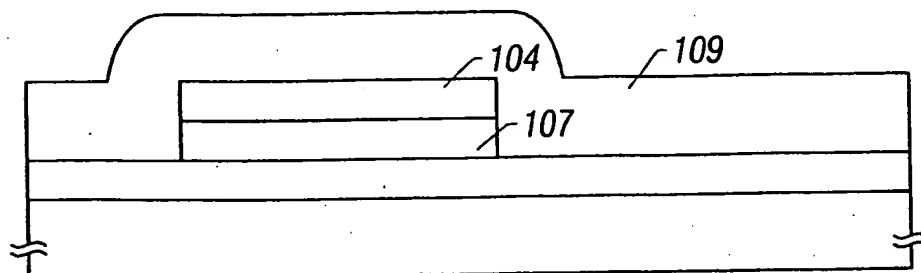


FIG. 1E



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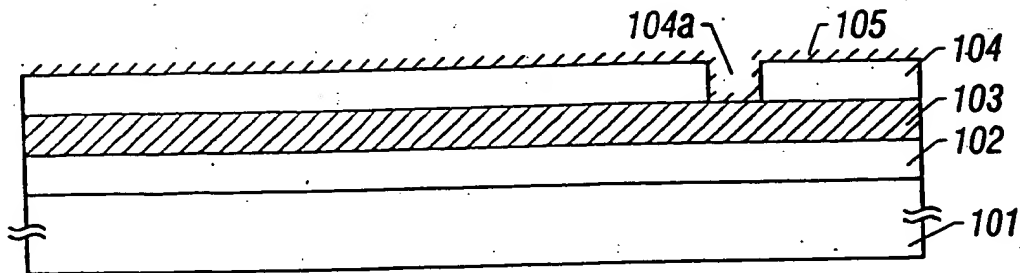


FIG. 1A

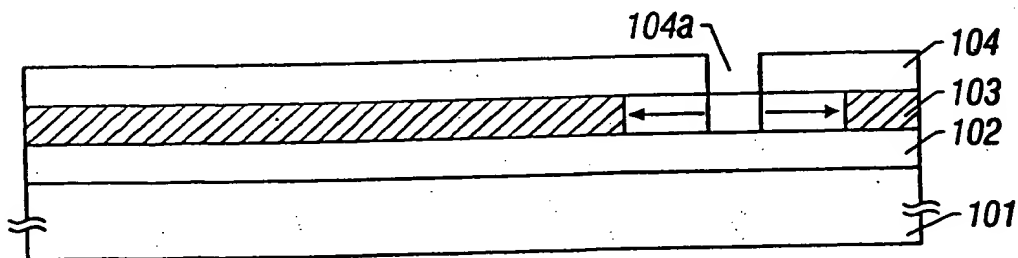


FIG. 1B

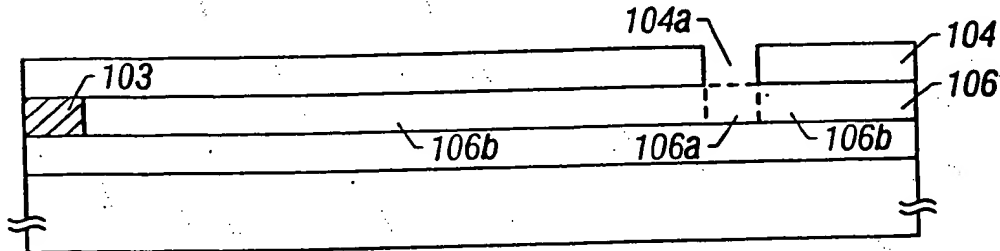


FIG. 1C

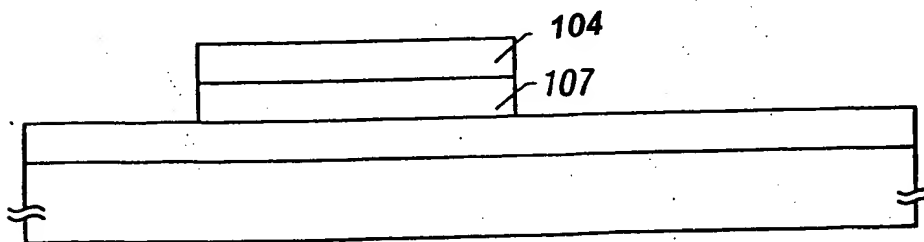


FIG. 1D

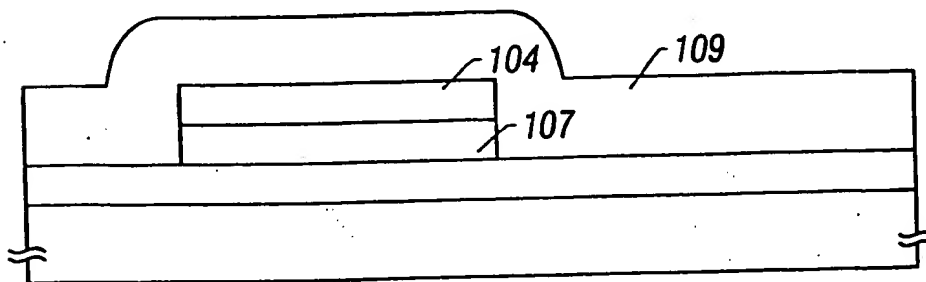


FIG. 1E



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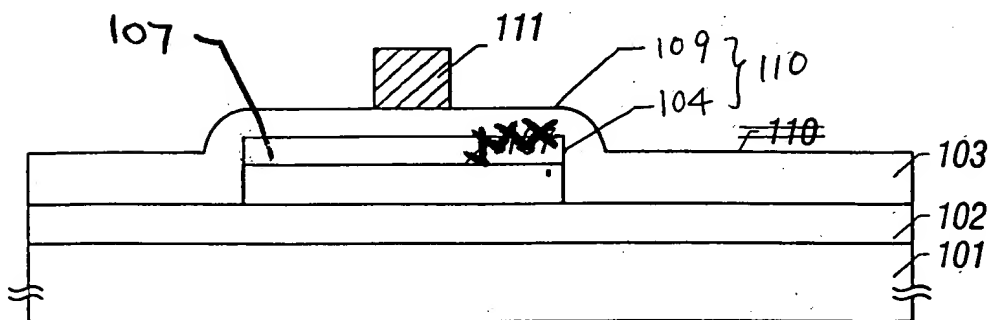


FIG. 2A

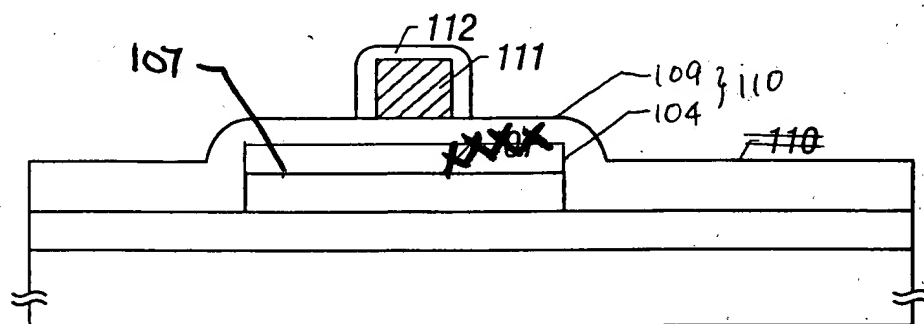


FIG. 2B

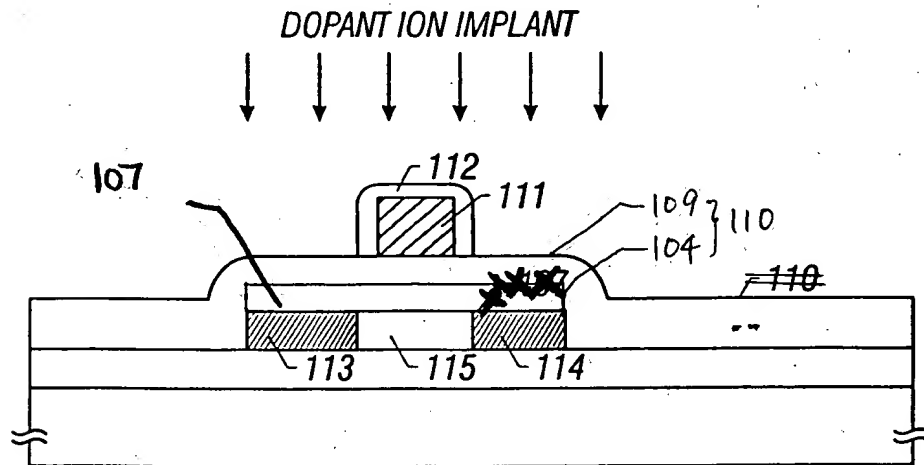


FIG. 2C

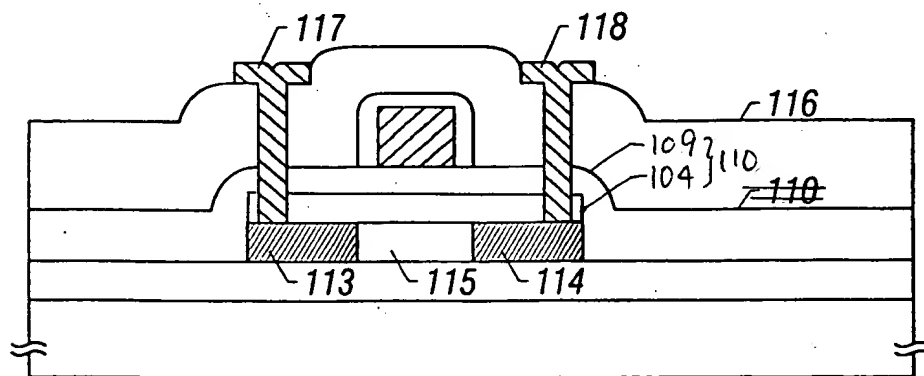
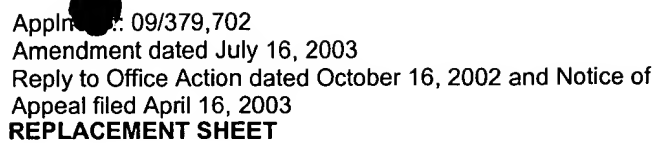


FIG. 2D



A cross-sectional view of a semiconductor device. A central block 111 is covered by a top layer 112. A contact 107 is formed on the top surface of block 111. The device is connected to a base 104 via a contact 109. The base 104 is connected to a power supply (indicated by a battery symbol).

[illegible][illegible]

FIG. 2D